

N- AND P-Channel Enhancement Mode MOSFET

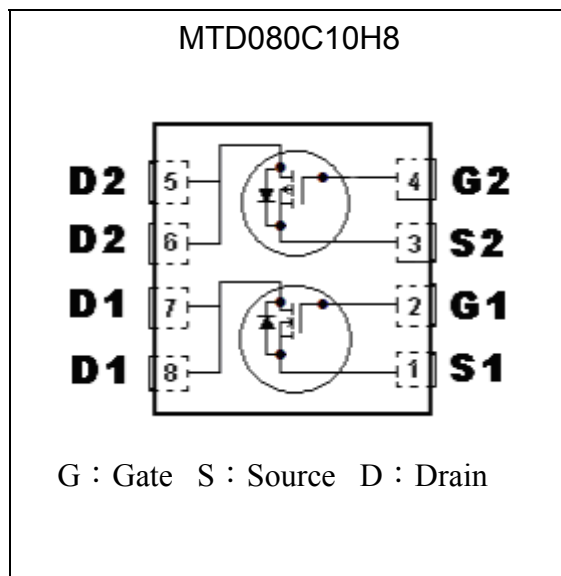
MTD080C10H8

Features

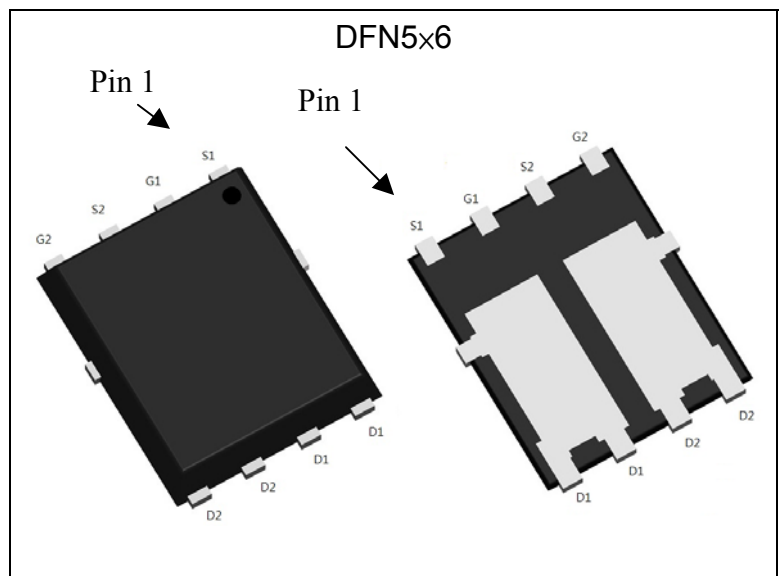
- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free lead plating and halogen-free package

	N-CH	P-CH
BV_{DSS}	100V	-100V
$I_D@V_{GS}=10V(-10V), T_A=25^\circ C$	3.6A	-3.1A
$I_D@V_{GS}=10V(-10V), T_C=25^\circ C$	10.4A	-8.8A
$R_{DS(on)(typ)}@V_{GS}=10V(-10V)$	74m Ω	114m Ω
$R_{DS(on)(typ)}@V_{GS}=4.5V(-4.5V)$	82m Ω	128m Ω

Equivalent Circuit

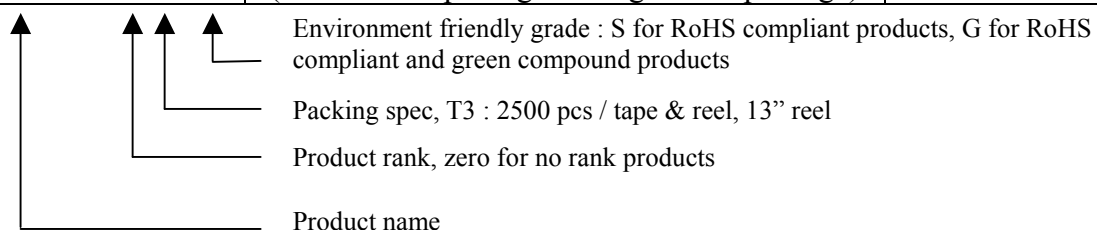


Outline



Ordering Information

Device	Package	Shipping
MTD080C10H8-0-T6-G	DFN 5 × 6 (Pb-free lead plating & halogen-free package)	3000 pcs / Tape & Reel



**Absolute Maximum Ratings** ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter		Symbol	Limits		Unit
			N-channel	P-channel	
Drain-Source Breakdown Voltage		BV _{DSS}	100	-100	V
Gate-Source Voltage		V _{GS}	±20	±20	
Continuous Drain Current	T _A =25 °C, V _{GS} =10V (-10V)	I _{DSM}	3.6	-3.1	A
	T _A =70 °C, V _{GS} =10V (-10V)		2.9	-2.5	
	T _C =25 °C, V _{GS} =10V (-10V)	I _D	10.4	-8.8	
	T _C =100 °C, V _{GS} =10V (-10V)		6.6	-5.6	
Pulsed Drain Current (Note 1 & 2)		I _{DM}	30	-28	
Power Dissipation	T _A =25 °C	P _{DSM}	2.5 (Note 3)		W
	T _A =70 °C		1.6 (Note 3)		
	T _C =25 °C	P _D	21		
	T _C =100 °C		8.4		
Operating Junction and Storage Temperature Range		T _j ; T _{stg}	-55~+150		°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	$R_{\theta JC}$	6	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-ambient, max	$R_{\theta JA}$	50 (Note 3)	

- Note : 1. Pulse width limited by maximum junction temperature
 2. Duty cycle $\leq 1\%$
 3. Surface mounted on 1 in² copper pad of FR-4 board; $125^{\circ}\text{C}/\text{W}$ when mounted on minimum copper pad.

N-Channel Electrical Characteristics ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	100	-	-	V	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$
$V_{GS(th)}$	1.5	-	2.5		$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$
I_{GSS}	-	-	± 100	nA	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$
I_{DSS}	-	-	1	μA	$V_{DS}=80\text{V}$, $V_{GS}=0\text{V}$
	-	-	25		$V_{DS}=80\text{V}$, $V_{GS}=0\text{V}$, $T_j=125^{\circ}\text{C}$
$*R_{DS(on)}$	-	74	98	m Ω	$I_D=2\text{A}$, $V_{GS}=10\text{V}$
	-	82	123		$I_D=1.5\text{A}$, $V_{GS}=5\text{V}$
$*G_{FS}$	-	5	-	S	$V_{DS}=10\text{V}$, $I_D=2\text{A}$
Dynamic					
C_{iss}	-	331	-	pF	$V_{DS}=50\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$
C_{oss}	-	41	-		
C_{rss}	-	18	-		
$*t_{d(on)}$	-	6.6	-	ns	$V_{DS}=50\text{V}$, $I_D=2\text{A}$, $V_{GS}=10\text{V}$, $R_G=1\Omega$
$*t_r$	-	17	-		
$*t_{d(off)}$	-	210.8	-		
$*t_f$	-	166.4	-		



*Qg	-	9.1	-	nC	V _{DS} =80V, I _D =2A, V _{GS} =10V
*Qgs	-	1.5	-		
*Qgd	-	2.6	-		
Body Diode					
*I _S	-	-	3.6	A	
*I _{SM}	-	-	14.4		
*V _{SD}	-	0.78	1.2	V	V _{GS} =0V, I _S =2A
*trr	-	20.8	-	ns	I _F =2A, dI _F /dt=100A/μs
*Q _{rr}	-	19.9	-	nC	

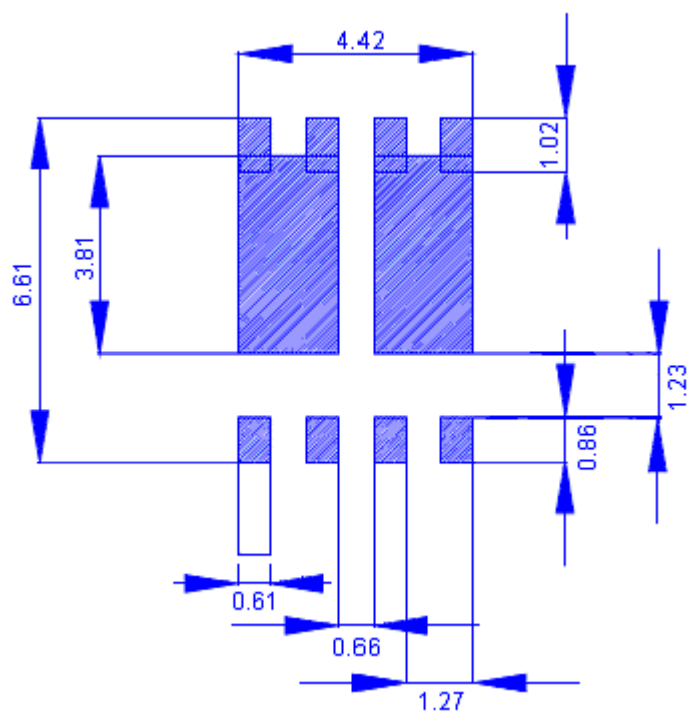
*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

P-Channel Electrical Characteristics (T_c=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-100	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-1.0	-	-2.6		V _{DS} =V _{GS} , I _D =-250μA
I _{GSS}	-	-	±10	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-80V, V _{GS} =0V
	-	-	-25		V _{DS} =-80V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	114	145	mΩ	I _D =-2A, V _{GS} =-10V
	-	128	179		I _D =-1.5A, V _{GS} =-4.5V
*G _{FS}	-	6.7	-	S	V _{DS} =-10V, I _D =-2A
Dynamic					
C _{iss}	-	749	-	pF	V _{DS} =-50V, V _{GS} =0V, f=1MHz
C _{oss}	-	66	-		
C _{rss}	-	36	-		
*t _{d(ON)}	-	7	-	ns	V _{DS} =-50V, I _D =-2A, V _{GS} =-10V, R _G =1 Ω
*t _r	-	18.8	-		
*t _{d(OFF)}	-	45.8	-		
*t _f	-	19.4	-		
*Q _g	-	18.2	-	nC	V _{DS} =-80V, I _D =-2A, V _{GS} =-10V
*Q _{gs}	-	2.3	-		
*Q _{gd}	-	4.2	-		
Body Diode					
*I _S	-	-	-3.1	A	
*I _{SM}	-	-	-12.4		
*V _{SD}	-	-0.78	-1.2	V	V _{GS} =0V, I _S =-2.5A
*t _{rr}	-	17.9	-	ns	I _F =-2A, dI _F /dt=100A/μs
*Q _{rr}	-	15.4	-	nC	

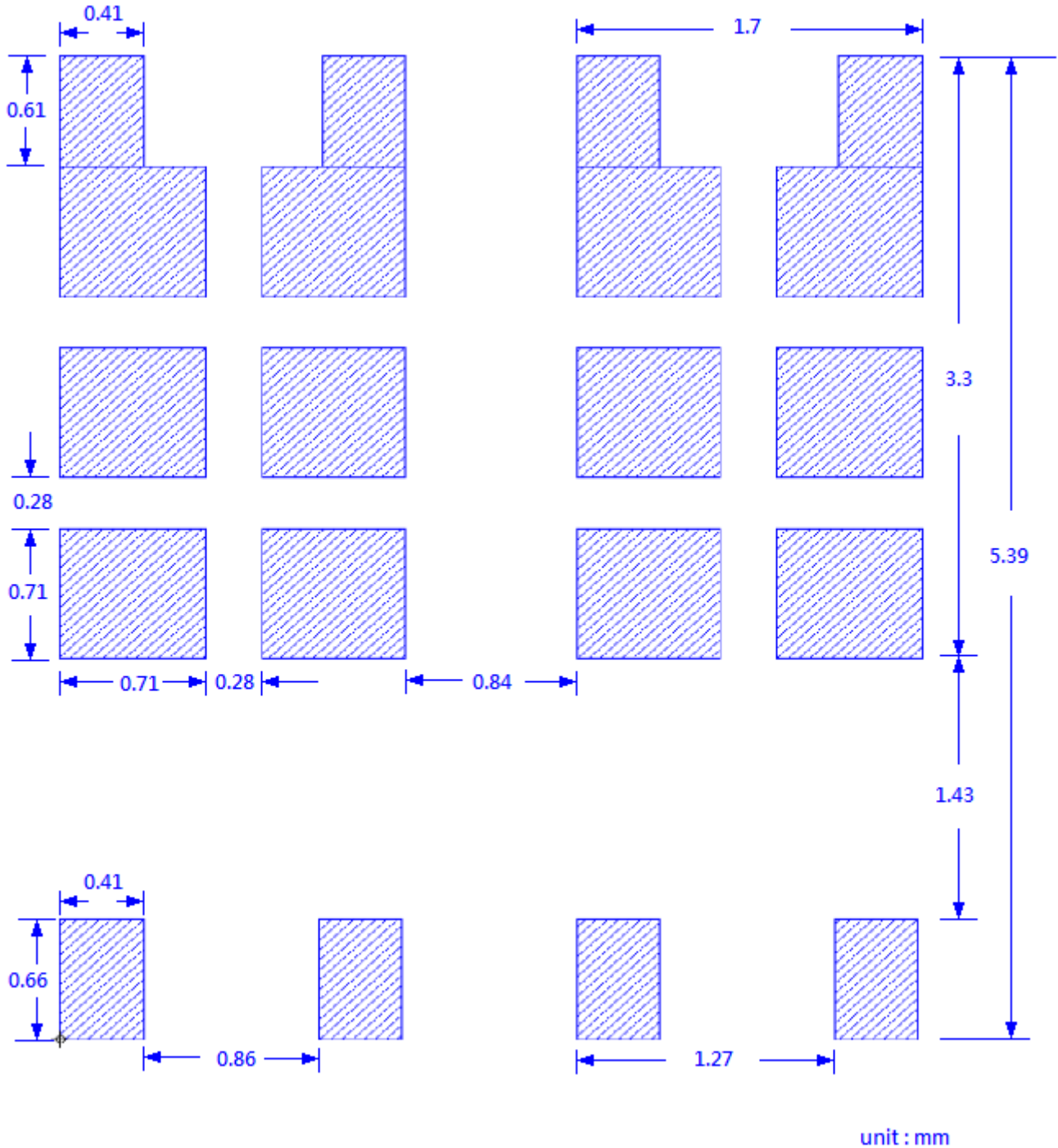
*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%

Recommended Soldering Footprint



unit : mm

Recommended Stencil Design

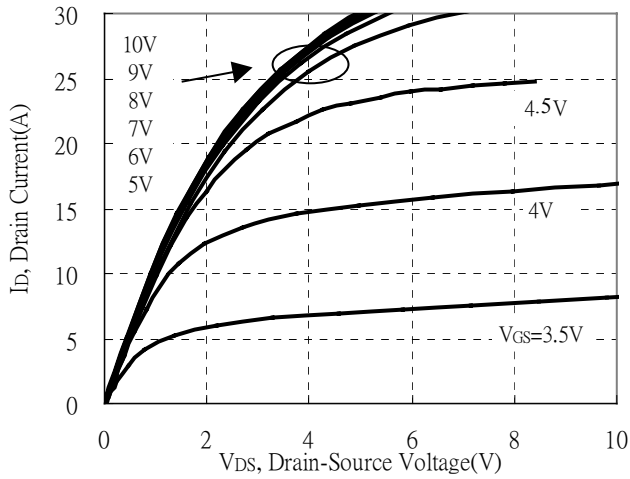


Note : 1. Stencil thickness 5 mil (0.127mm)

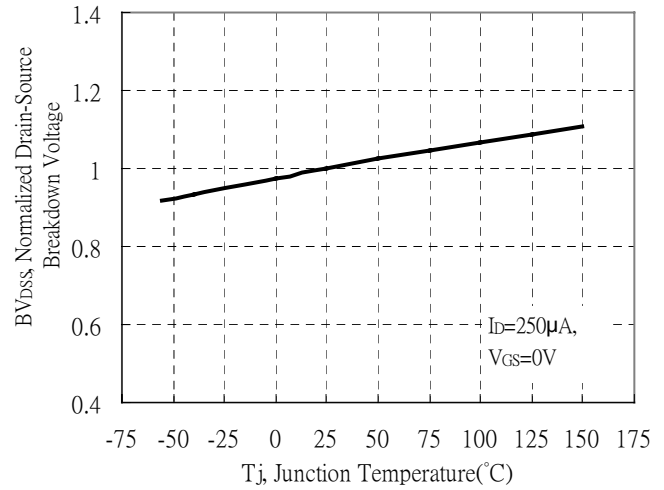
2. May need to be adjusted to specific requirements.

Typical Characteristics : Q1(N-channel)

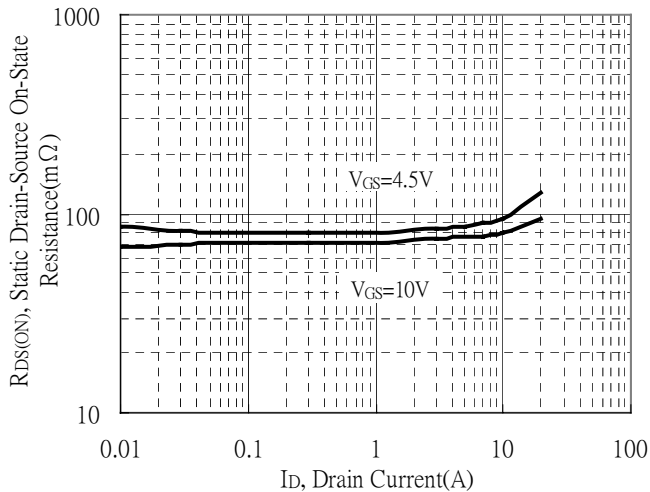
Typical Output Characteristics



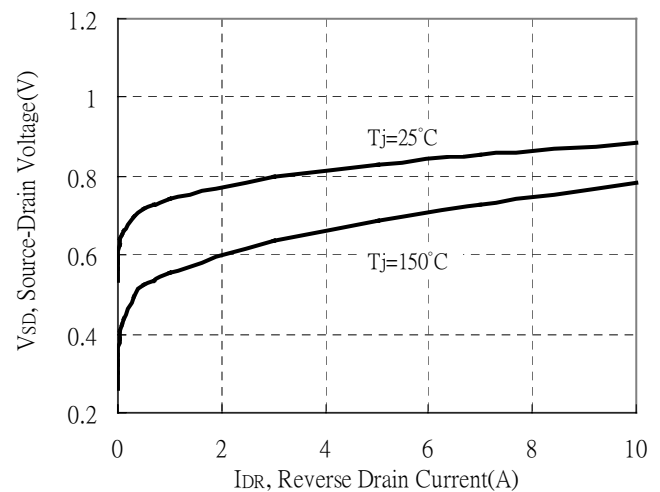
Breakdown Voltage vs Ambient Temperature



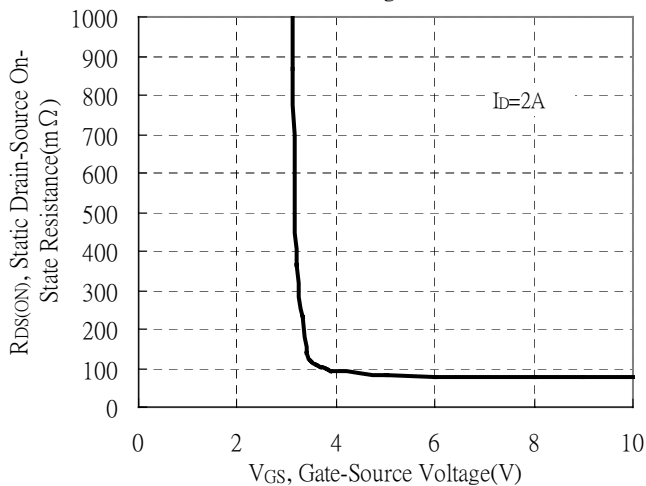
Static Drain-Source On-State resistance vs Drain Current



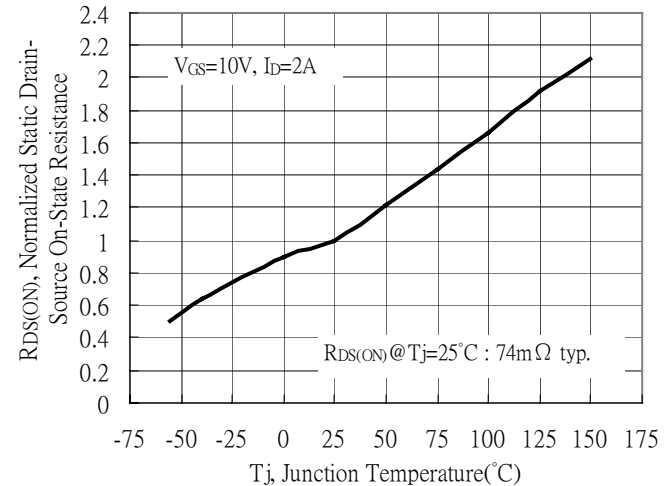
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

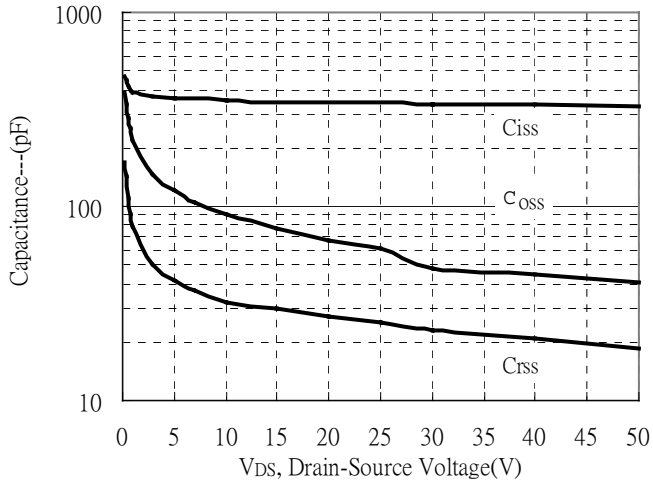


Drain-Source On-State Resistance vs Junction Temperature

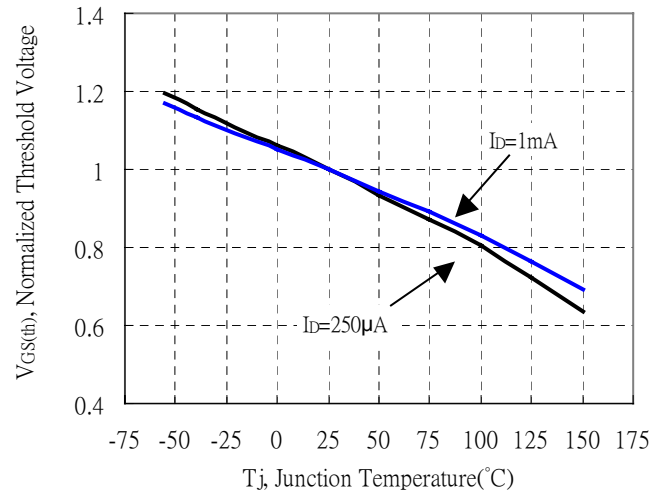


Typical Characteristics(Cont.) : Q1(N-channel)

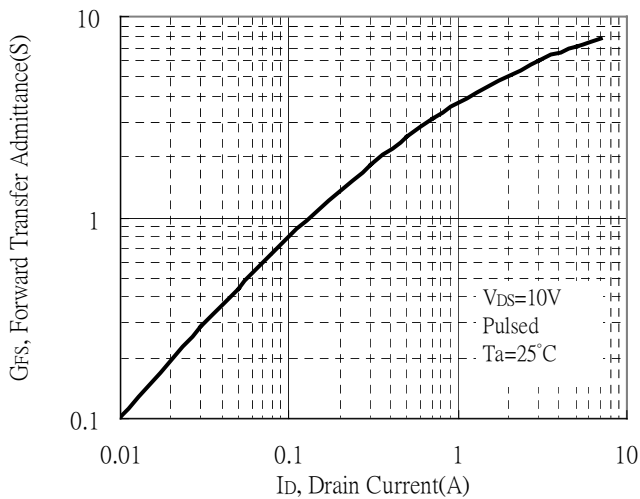
Capacitance vs Drain-to-Source Voltage



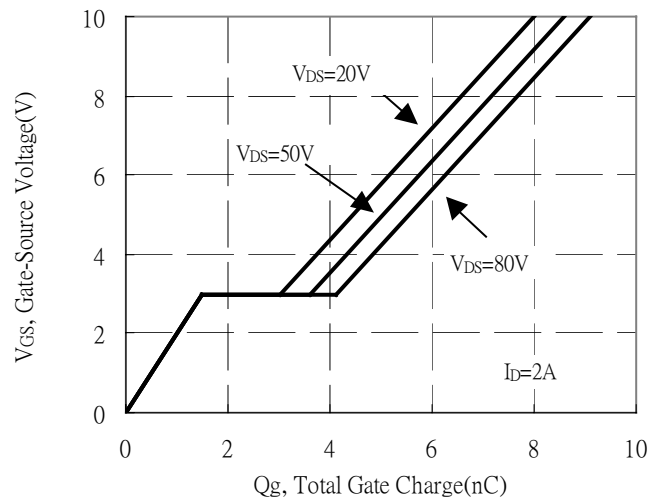
Threshold Voltage vs Junction Temperature



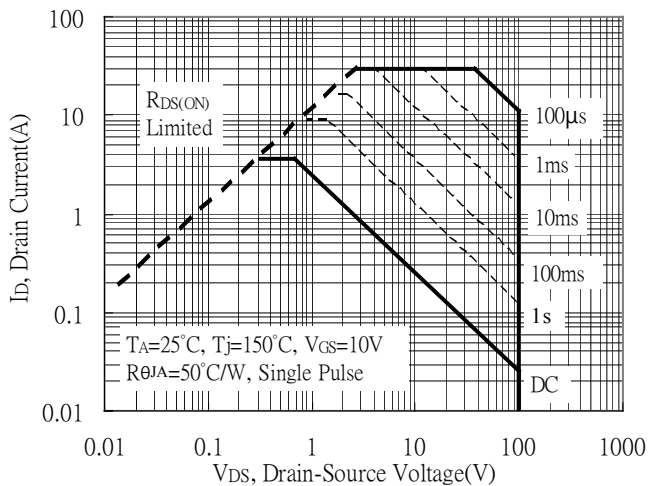
Forward Transfer Admittance vs Drain Current



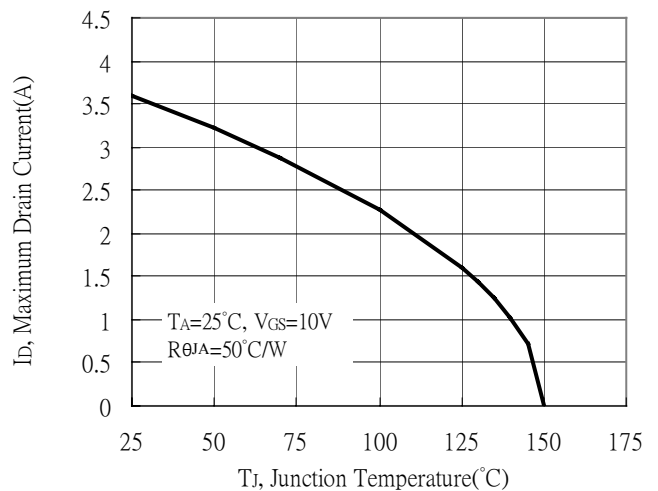
Gate Charge Characteristics



Maximum Safe Operating Area

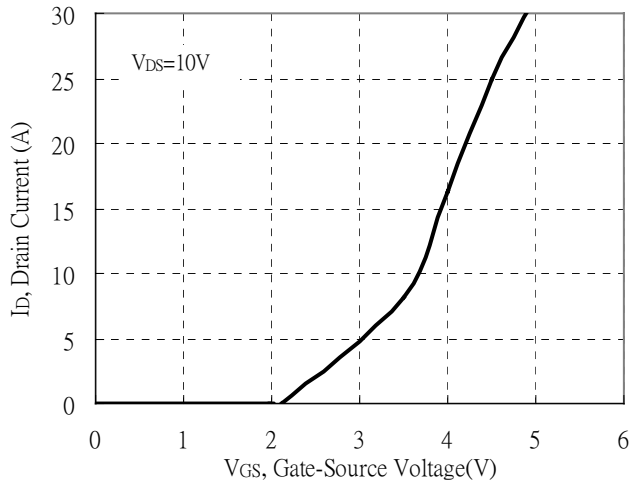


Maximum Drain Current vs Junction Temperature

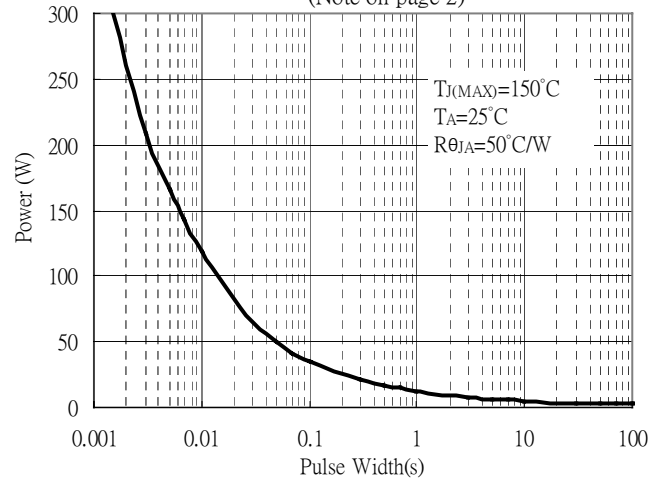


Typical Characteristics(Cont.) : Q1(N-channel)

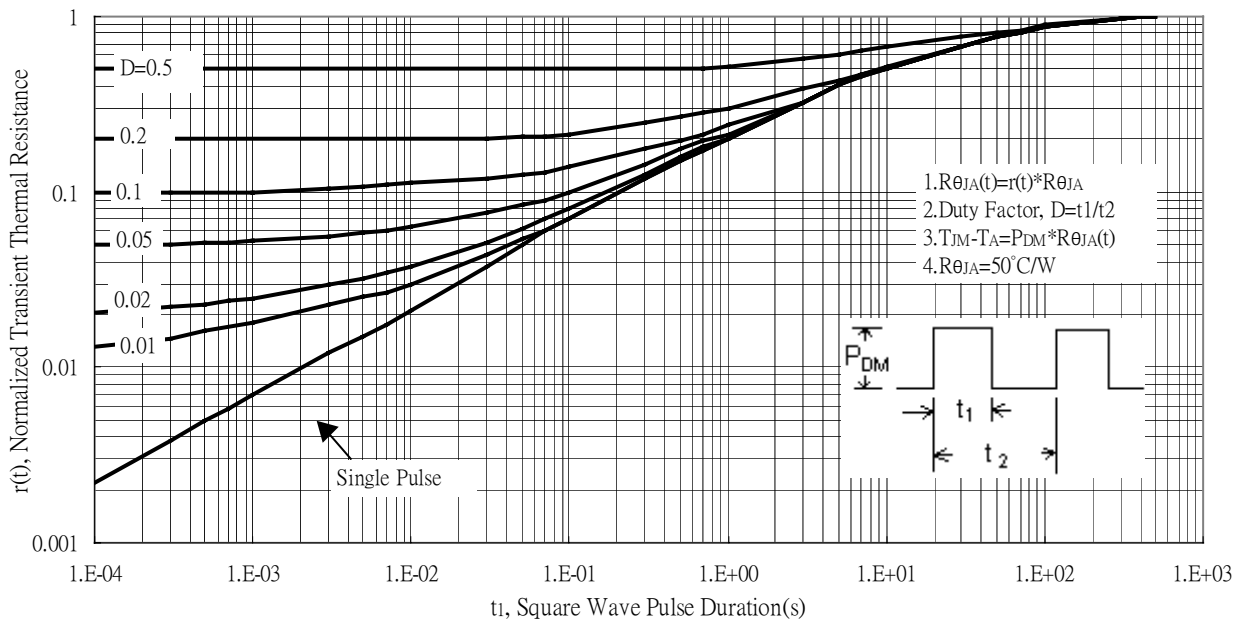
Typical Transfer Characteristics



Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)

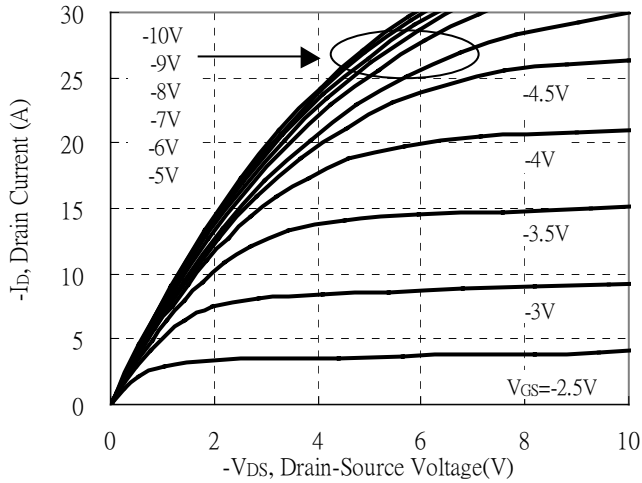


Transient Thermal Response Curves

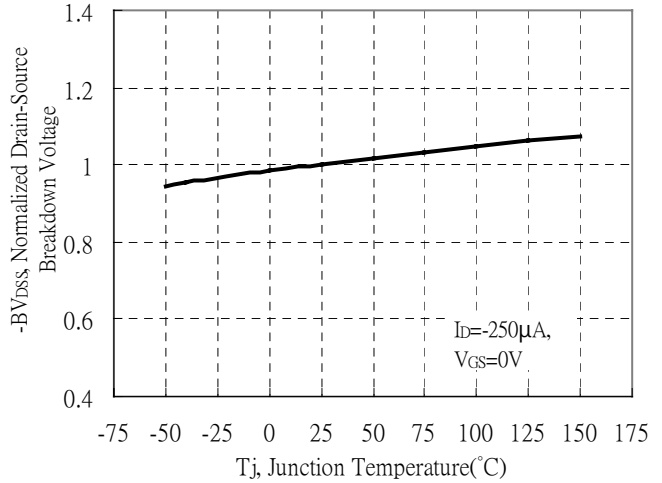


Typical Characteristics : Q2(P-channel)

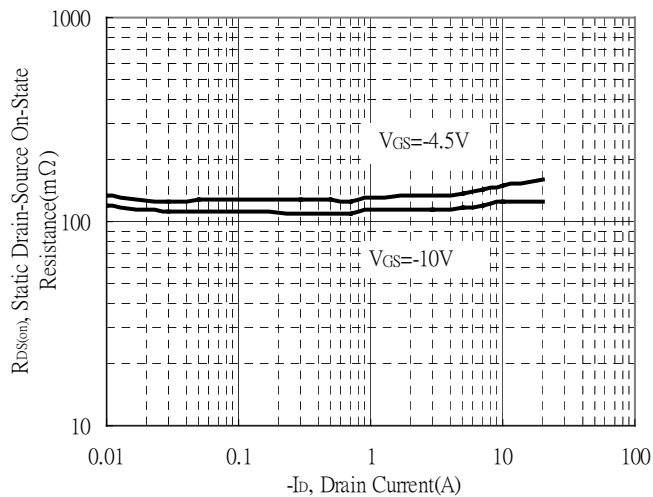
Typical Output Characteristics



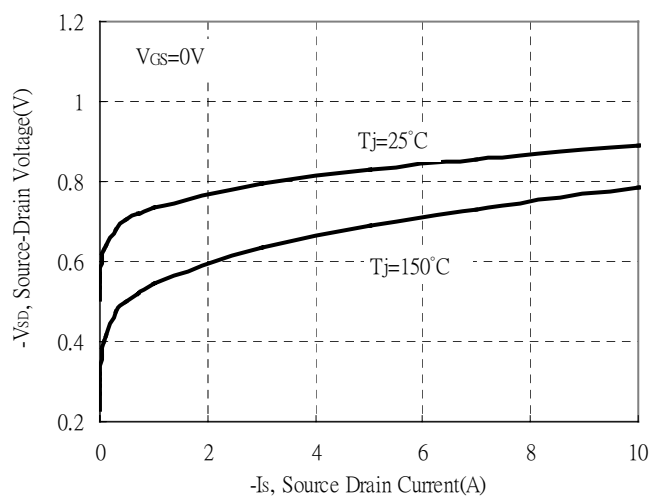
Breakdown Voltage vs Ambient Temperature



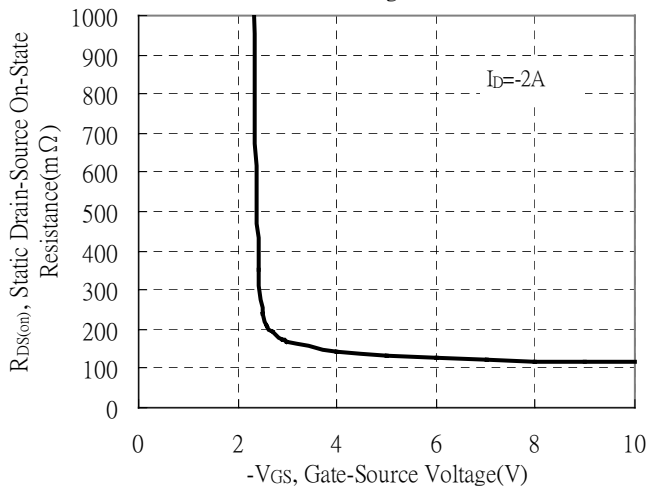
Static Drain-Source On-State resistance vs Drain Current



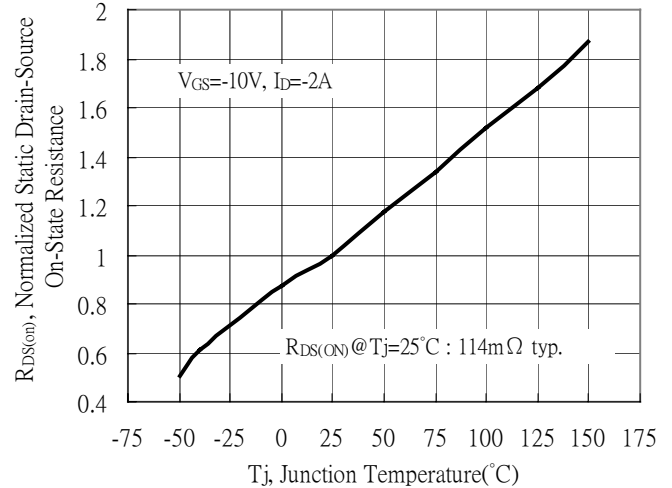
Source Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

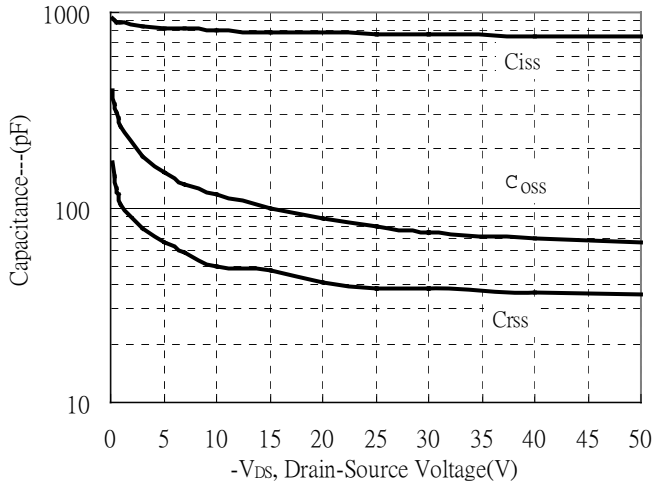


Drain-Source On-State Resistance vs Junction Temperature

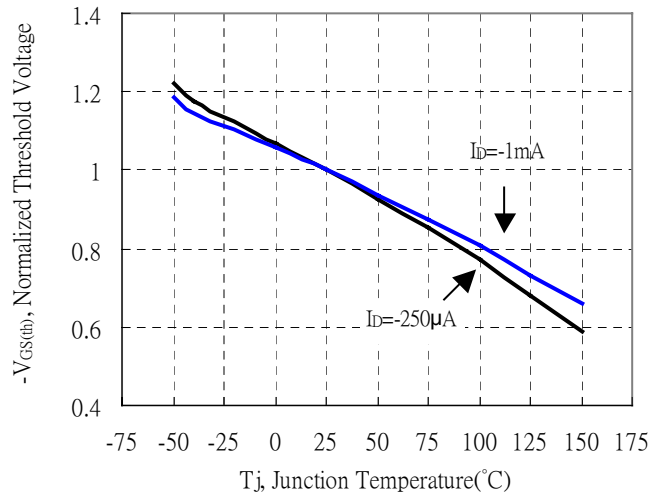


Typical Characteristics(Cont.) : Q2(P-channel)

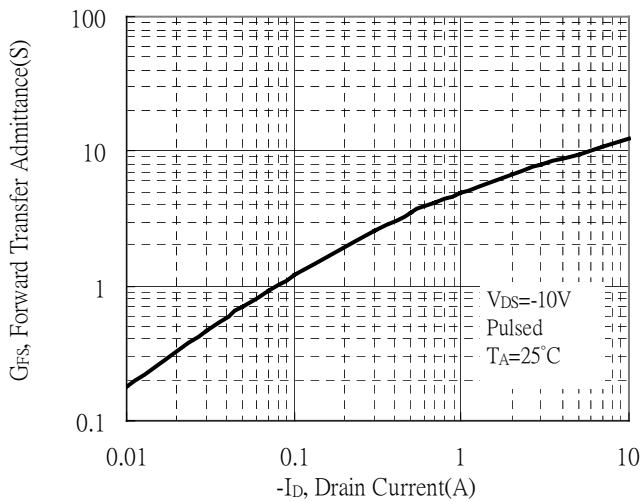
Capacitance vs Drain-to-Source Voltage



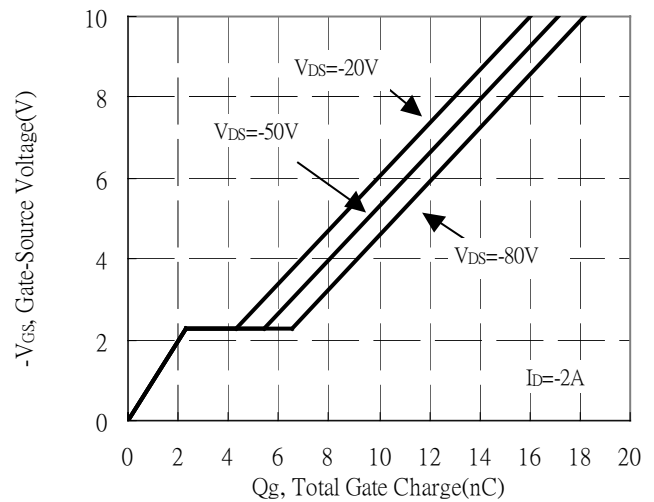
Threshold Voltage vs Junction Temperature



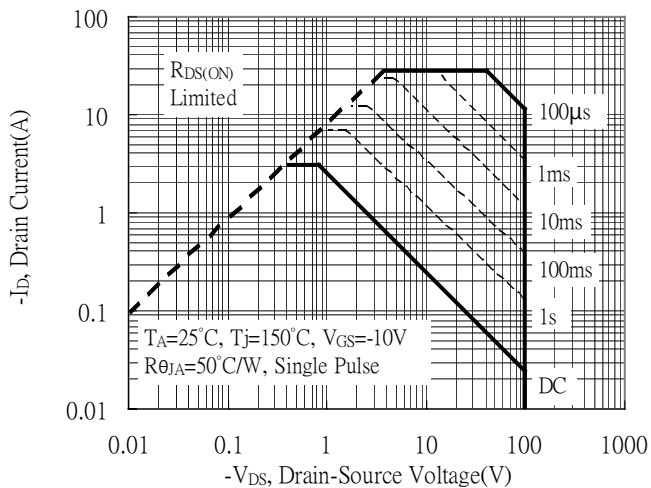
Forward Transfer Admittance vs Drain Current



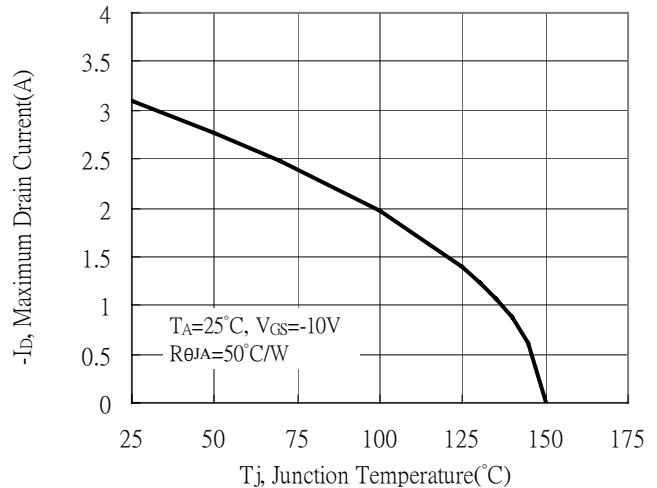
Gate Charge Characteristics



Maximum Safe Operating Area

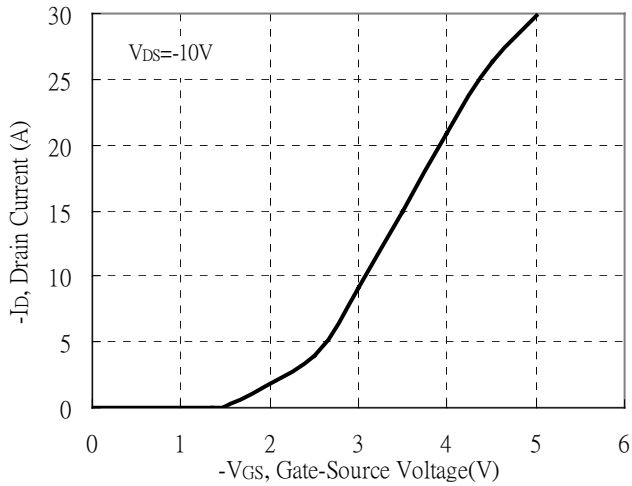


Maximum Drain Current vs Junction Temperature

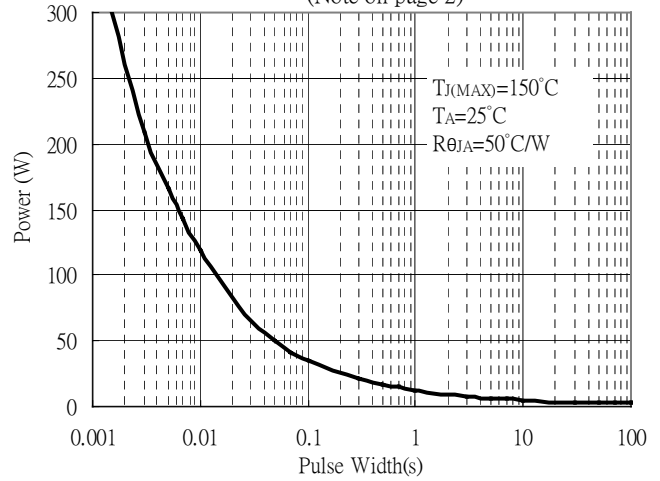


Typical Characteristics(Cont.) : Q2(P-channel)

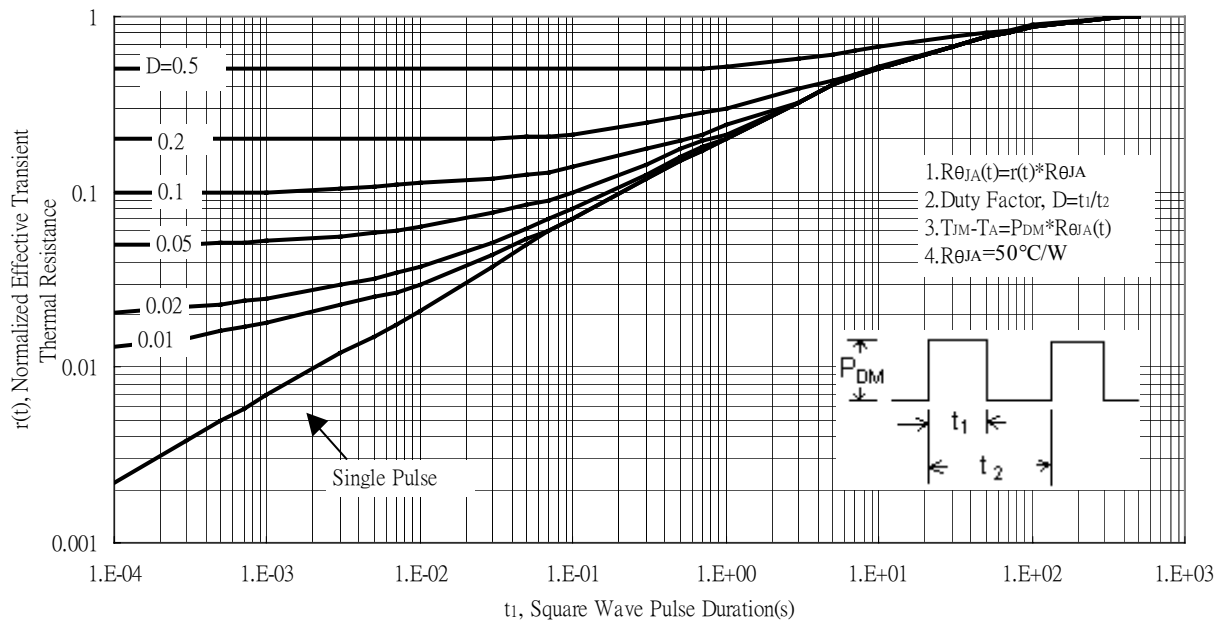
Typical Transfer Characteristics

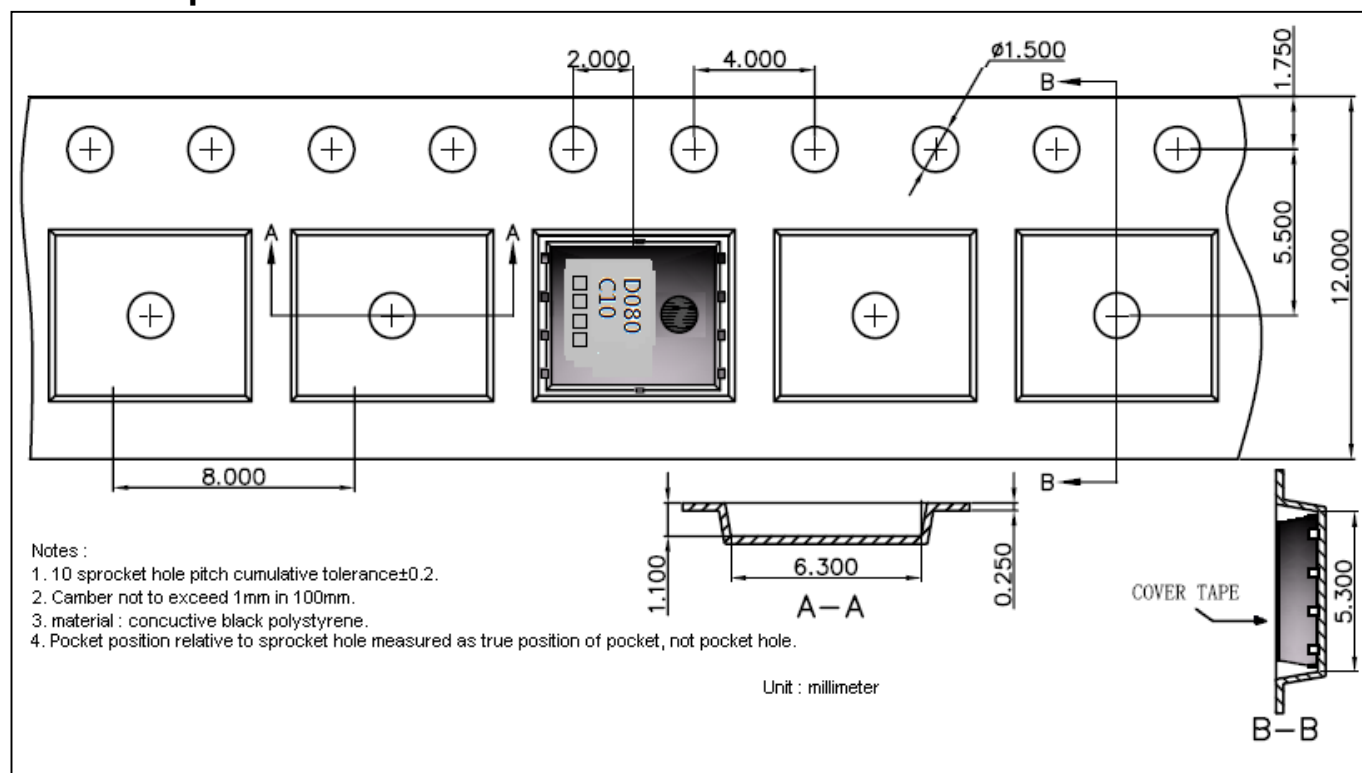
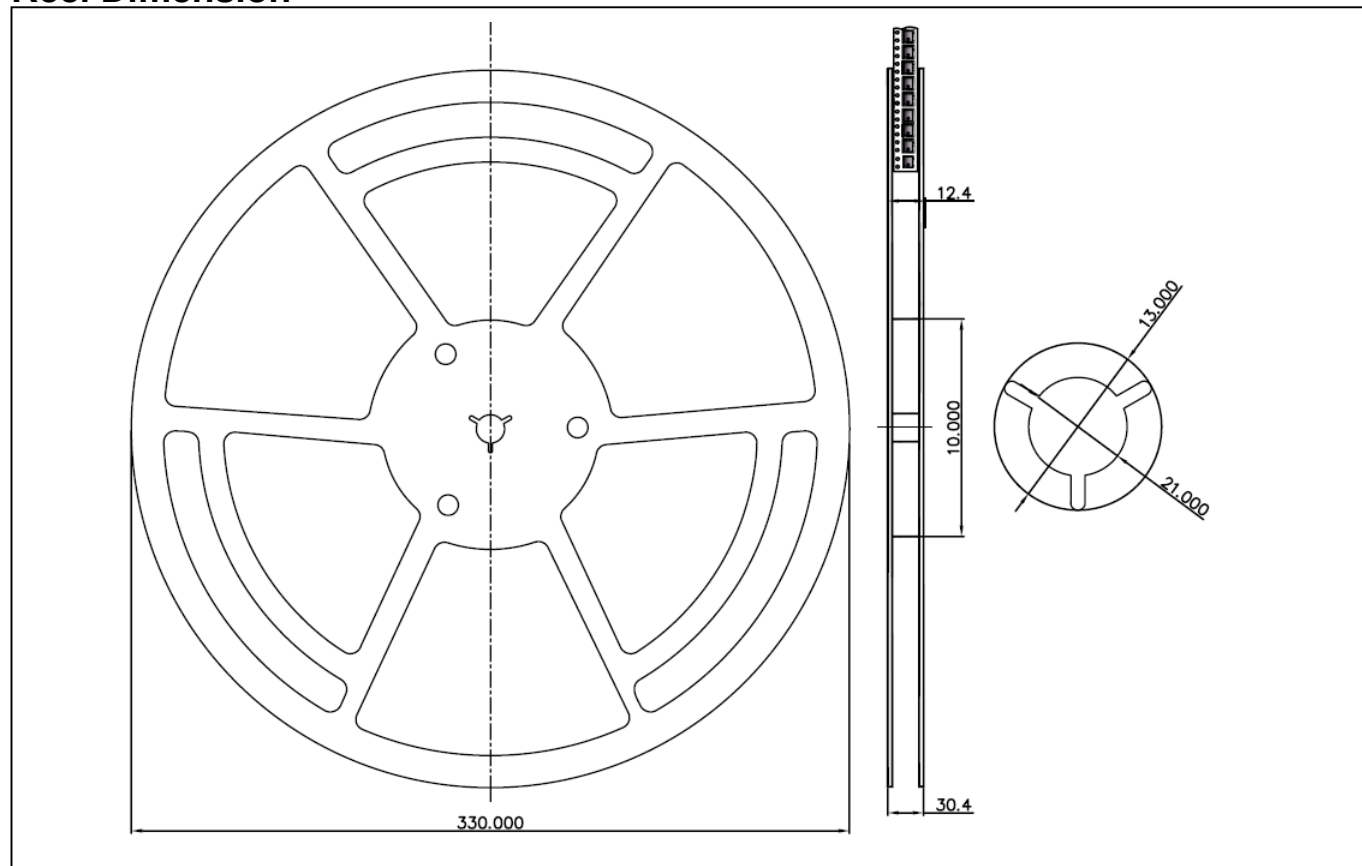


Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



Transient Thermal Response Curves

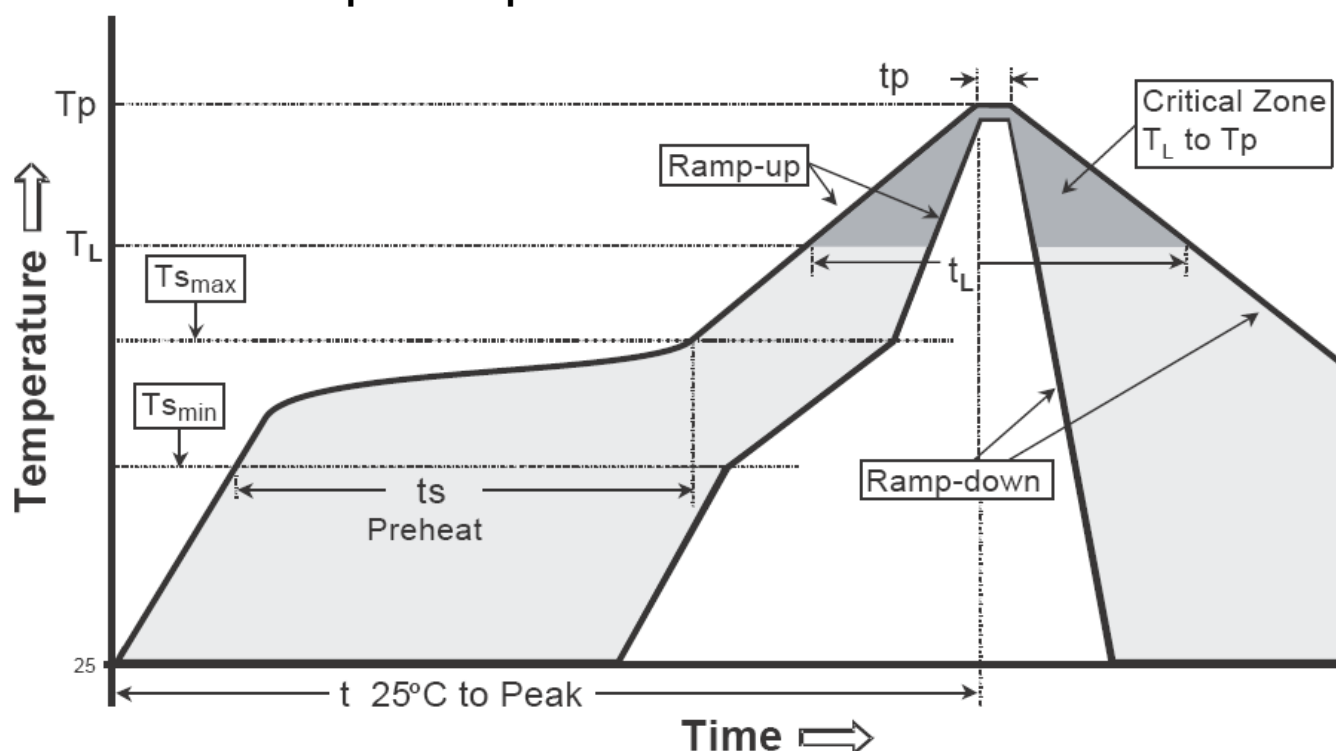




Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

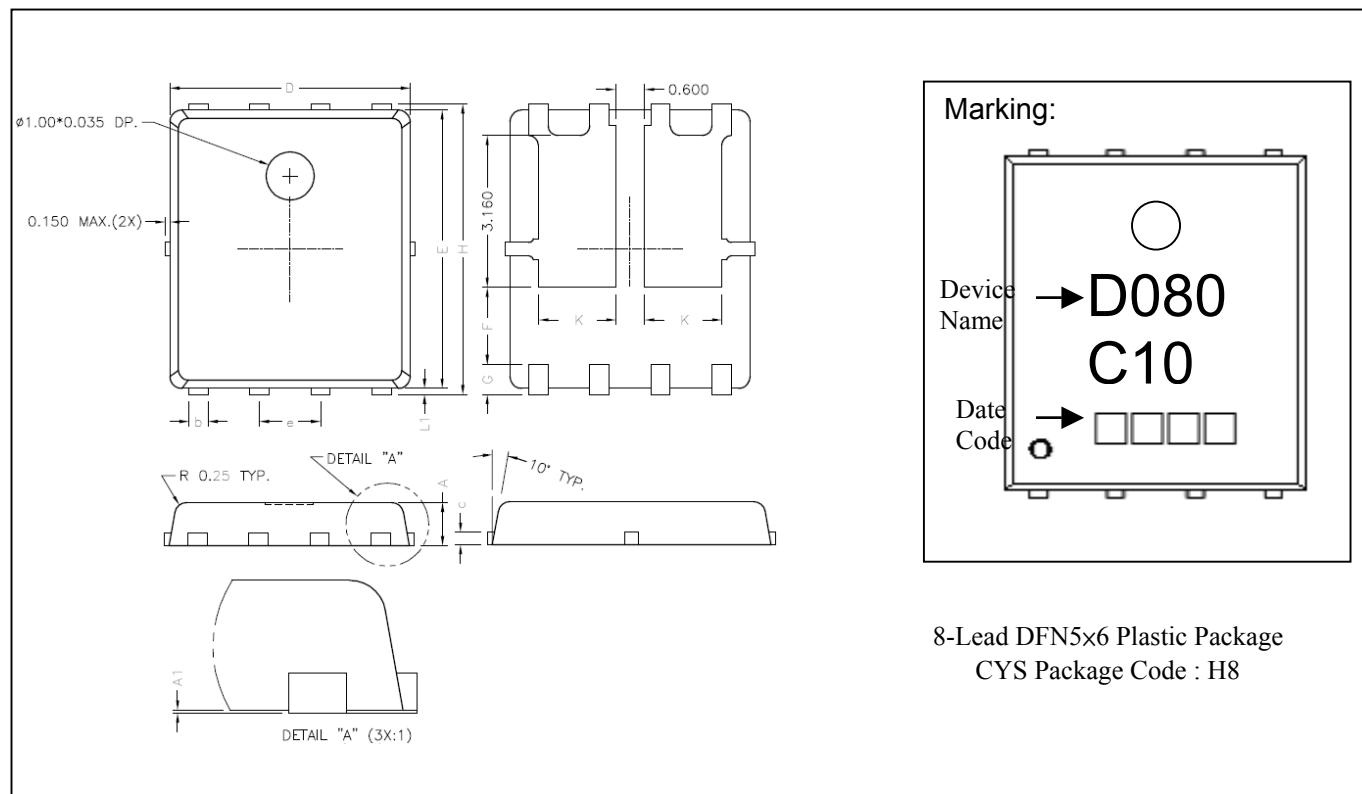
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (Tl)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

DFN5x6 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.80	1.00	0.031	0.039	E	5.70	5.90	0.224	0.232
A1	0.00	0.05	0.000	0.002	e	1.27	BSC	0.050	BSC
b	0.35	0.49	0.014	0.019	H	5.95	6.20	0.234	0.244
c	0.254	REF	0.010	REF	L1	0.10	0.18	0.004	0.007
D	4.90	5.10	0.193	0.201	G	0.60	REF	0.024	REF
F	1.60	REF	0.063	REF	K	1.60	REF	0.063	REF

Notes: 1. Controlling dimension: millimeters.

2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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